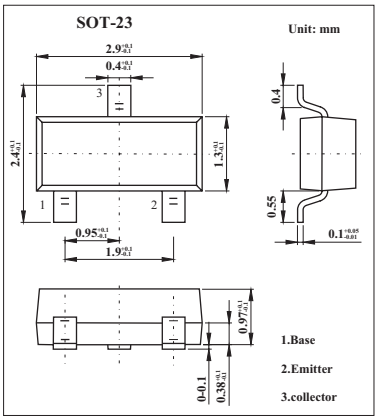
General Purpose Transistor

BCX71G



■ Features

●PNP Epitaxial Silicon Transistor

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-45	V
Collector-emitter voltage	V_{CEO}	-45	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-100	mA
Collector Power Dissipation	P_C	350	mW
Storage Temperature	T_{STG}	150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	B_{VCEO}	I_C= -2mA, I_B=0	-45			V
Emitter-Base Breakdown Voltage	B_{VEBO}	I_E= -1μA, I_C=0	-5			V
Collector Cut-off Current	I_{CES}	V_{CE}= -32V, V_{BE}=0			-20	nA
DC Current Gain	h_{FE}	V_{CE}= -5V, I_C= -2mA	120		220	
		V_{CE}= -1V, I_C= -50μA	60			
Collector-Emitter Saturation Voltage	$V_{CE\ (sat)}$	I_C= -10mA, I_B= -0.25mA			-0.25	V
		I_C= -50mA, I_B= -1.25mA			-0.55	V
Base-Emitter Saturation Voltage	$V_{BE\ (sat)}$	I_C= -10mA, I_B= -0.25mA	-0.6		-0.85	V
		I_C= -50mA, I_B= -1.25mA	-0.68		-1.05	V
Base-Emitter On Voltage	$V_{BE\ (on)}$	V_{CE}= -5V, I_C= -2mA	-0.6		-0.75	V
Output Capactance	C_{ob}	V_{CB}= -10V, I_E=0, f=1MHz				pF
Noise Figure	N_F	I_C=0.2mA, V_{CE}=5V,f=1KHz, RS=2KΩ			6	dB
Turn On Time	t_{ON}	I_C= -10mA, I_{B1}= -1mA			150	ns
Turn Off Time	t_{OFF}	I_{B2}= -1mA, V_{BB}=3.6V,R_L=990Ω			800	ns

■ Marking

Marking	BG